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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HD74LVC244A

Octal Buffers / Line Drivers with 3-state Outputs



ADE-205-110B(Z)

3rd Edition
December 1996

Description

The HD74LVC244A has eight line drivers with three state outputs in a 20 pin package. This device is a non inverting buffer and has two active low enables ($\overline{1G}$ and $\overline{2G}$). Each enable independently controls four buffers. Low voltage and high speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{CC} = 2.0\text{ V to }5.5\text{ V}$
- All inputs $V_{IH}(\text{Max.}) = 5.5\text{ V}$ ($@V_{CC} = 0\text{ V to }5.5\text{ V}$)
- All outputs $V_{OUT}(\text{Max.}) = 5.5\text{ V}$ ($@V_{CC} = 0\text{ V}$ or output off state)
- Typical V_{OL} ground bounce $< 0.8\text{ V}$ ($@V_{CC} = 3.3\text{ V}$, $T_a = 25^\circ\text{C}$)
- Typical V_{OH} undershoot $> 2.0\text{ V}$ ($@V_{CC} = 3.3\text{ V}$, $T_a = 25^\circ\text{C}$)
- High output current $\pm 24\text{ mA}$ ($@V_{CC} = 3.0\text{ V to }5.5\text{ V}$)

Function Table

Inputs		Output Y
\overline{G}	A	
H	X	Z
L	H	H
L	L	L

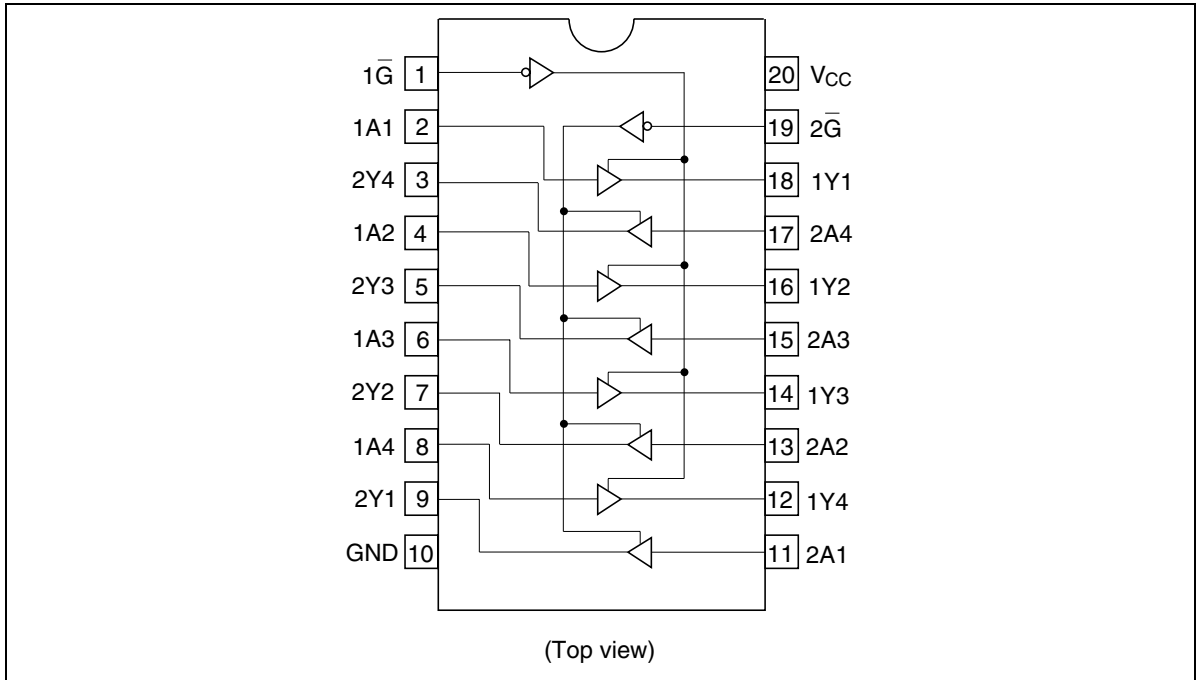
H: High level

L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	-0.5 to 6.0	V	
Input diode current	I_{IK}	-50	mA	$V_I = -0.5$ V
Input voltage	V_I	-0.5 to 6.0	V	
Output diode current	I_{OK}	-50	mA	$V_O = -0.5$ V
		50	mA	$V_O = V_{CC} + 0.5$ V
Output voltage	V_O	-0.5 to $V_{CC} + 0.5$	V	Output "H" or "L"
		-0.5 to 6.0	V	Output "Z" V_{CC} :OFF
Output current	I_O	± 50	mA	
V_{CC} , GND current / pin	I_{CC} or I_{GND}	100	mA	
Storage temperature	T_{stg}	-65 to 150	$^{\circ}$ C	

Note: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{cc}	1.5 to 5.5	V	Data retention
		2.0 to 5.5	V	At operation
Input / output voltage	V_I	0 to 5.5	V	\bar{G}_1, A
	V_O	0 to V_{cc}	V	Output "H" or "L"
		0 to 5.5	V	Output "Z" or V_{cc} :OFF
Operating temperature	T_a	-40 to 85	°C	
Output current	I_{OH}	-12	mA	$V_{cc} = 2.7 V$
		-24 ²	mA	$V_{cc} = 3.0 V$ to 5.5 V
	I_{OL}	12	mA	$V_{cc} = 2.7 V$
		24 ²	mA	$V_{cc} = 3.0 V$ to 5.5 V
Input rise / fall time ¹	t_r, t_f	10	ns/V	

Notes: 1. This item guarantees maximum limit when one input switches.

Waveform : Refer to test circuit of switching characteristics.

2. duty cycle $\leq 50\%$

Electrical Characteristics

Ta = -40 to 85°C

Item	Symbol	V _{CC} (V)	Ta = -40 to 85°C		Unit	Test Conditions
			Min	Max		
Input voltage	V _{IH}	2.7 to 3.6	2.0	—	V	
		4.5 to 5.5	V _{CC} ×0.7	—	V	
	V _{IL}	2.7 to 3.6	—	0.8	V	
		4.5 to 5.5	—	V _{CC} ×0.3	V	
Output voltage	V _{OH}	2.7 to 5.5	V _{CC} -0.2	—	V	I _{OH} = -100 μA
		2.7	2.2	—	V	I _{OH} = -12 mA
		3.0	2.4	—	V	
		3.0	2.2	—	V	I _{OH} = -24 mA
		4.5	3.8	—	V	
	V _{OL}	2.7 to 5.5	—	0.2	V	I _{OL} = 100 μA
		2.7	—	0.4	V	I _{OL} = 12 mA
		3.0	—	0.55	V	I _{OL} = 24 mA
		4.5	—	0.55	V	
Input current	I _{IN}	0 to 5.5	—	±5.0	μA	V _{IN} = 5.5 V or GND
Off state output current	I _{OZ}	2.7 to 5.5	—	±5.0	μA	V _{IN} = V _{CC} , GND V _{OUT} = 5.5 V or GND
Output leak current	I _{OFF}	0	—	20	μA	V _{IN} / V _{OUT} = 5.5 V
Quiescent supply current	I _{CC}	2.7 to 3.6	—	±10	μA	V _{IN} / V _{OUT} = 3.6 to 5.5 V
		2.7 to 5.5	—	10	μA	V _{IN} = V _{CC} or GND
	ΔI _{CC}	3.0 to 3.6	—	500	μA	V _{IN} = one input at (V _{CC} -0.6)V, other inputs at V _{CC} or GND

Switching Characteristics

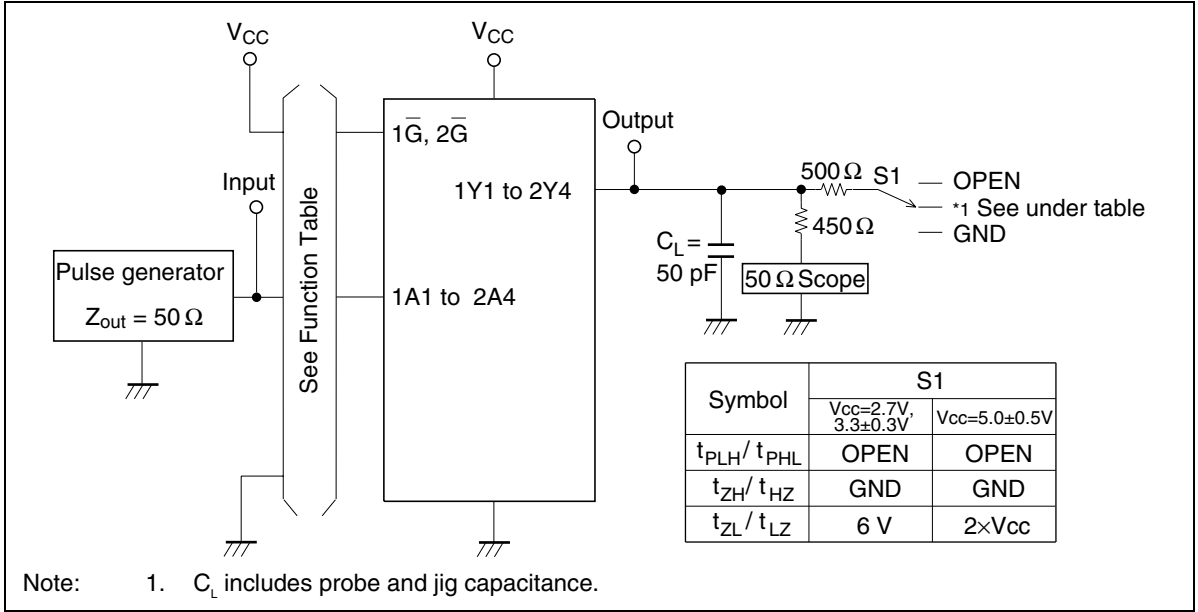
Ta = -40 to 85°C

Item	Symbol	V _{cc} (V)	Ta = -40 to 85°C			Unit	From (Input)	To (Output)
			Min	Typ	Max			
Propagation delay time	t _{PLH}	2.7	—	—	7.5	ns	A	Y
	t _{PHL}	3.3±0.3	1.5	—	6.5	ns		
		5.0±0.5	—	—	5.0	ns		
Output enable time	t _{ZH}	2.7	—	—	9.0	ns	\bar{G}	Y
	t _{ZL}	3.3±0.3	1.5	—	8.0	ns		
		5.0±0.5	—	—	6.5	ns		
Output disable time	t _{ZH}	2.7	—	—	8.0	ns	\bar{G}	Y
	t _{ZL}	3.3±0.3	1.5	—	7.0	ns		
		5.0±0.5	—	—	6.0	ns		
Between outut pins skew ^{*1}	t _{OSLH}	2.7	—	—	—	ns		
	t _{OSHL}	3.3±0.3	—	—	1.0	ns		
		5.0±0.5	—	—	1.0	ns		
Input capacitance	C _{IN}	2.7	—	3.0	—	pF		
Output capacitance	C _O	2.7	—	15.0	—	pF		

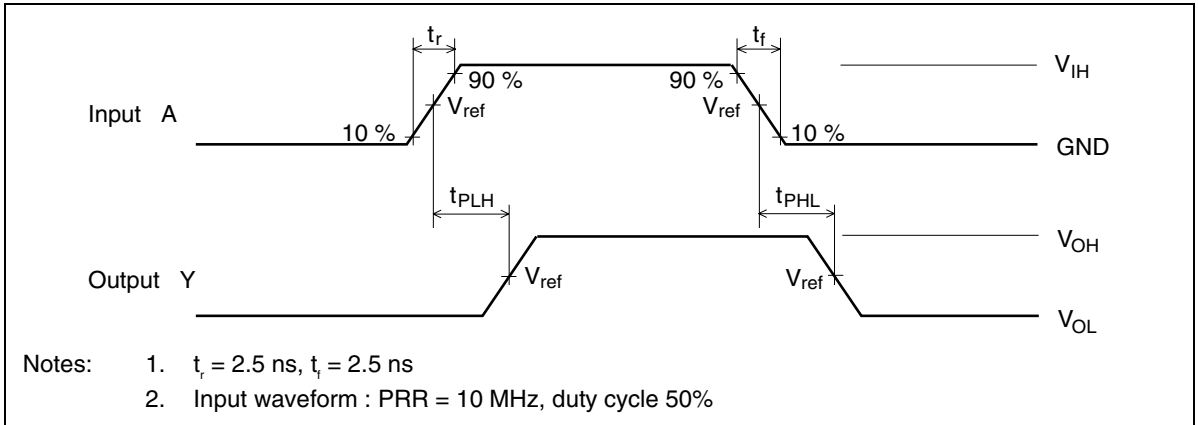
Note: 1. This parameter is characterized but not tested.

$$tos_{LH} = |t_{PLHm} - t_{PLHn}|, tos_{HL} = |t_{PHLm} - t_{PHLn}|$$

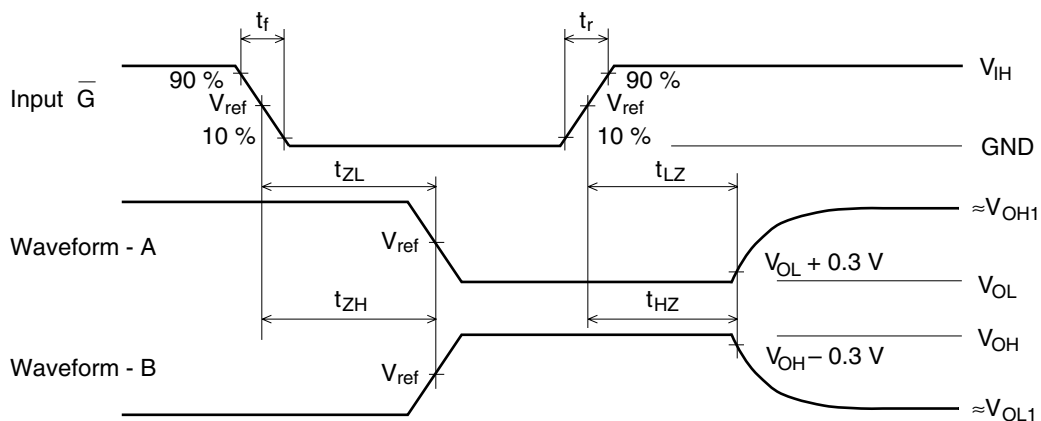
Test Circuit



Waveforms – 1



Waveforms – 2

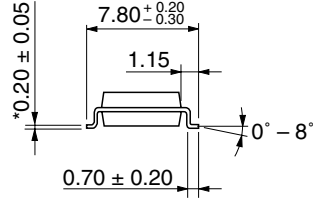
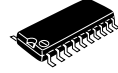
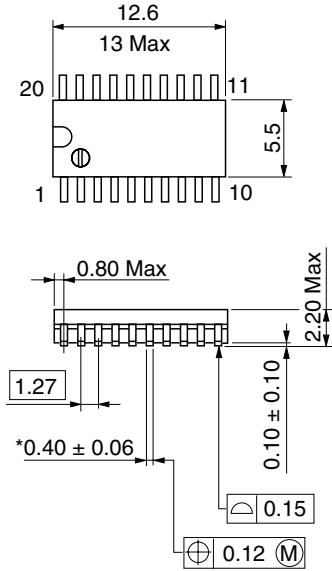


TEST	$V_{CC}=2.7V, 3.3\pm 0.3V$	$V_{CC}=5.0\pm 0.5V$
V_{IH}	2.7 V	V_{CC}
V_{ref}	1.5 V	50% V_{CC}
V_{OH1}	3 V	V_{CC}
V_{OL1}	GND	GND

- Notes:
1. $t_f = 2.5$ ns, $t_r = 2.5$ ns
 2. Input waveform : PRR = 10 MHz, duty cycle 50%
 3. Waveform – A shows input conditions such that the output is "L" level when enable by the output control.
 4. Waveform – B shows input conditions such that the output is "H" level when enable by the output control.

Package Dimensions

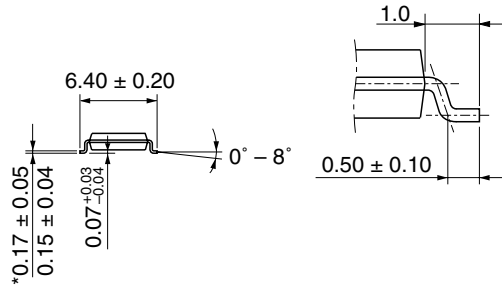
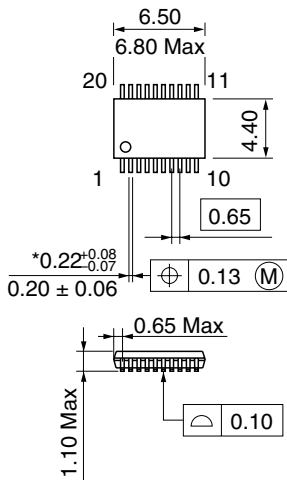
As of July, 2001
Unit: mm



*Pd plating

Hitachi Code	FP-20DAV
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.31 g

As of July, 2001
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
JEITA	—
Mass (reference value)	0.07 g

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